

AMENDMENTS TO THE CLAIMS

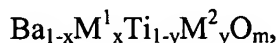
This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-18. (canceled)

Claim 19. (currently amended): A memory device, comprising:

a dielectric film comprising a quaternary metal oxide having a formula of:



wherein

M^1 is a metal selected from the group consisting of the elements of Group IA and IIA of the period table, lanthanide series, Zn, Bi, and Sn;

~~M^2 is a metal selected from the group consisting of Ta, Zr, Ce, Nb, Co, and Hf;~~

$0 < x, y < 1$; and

m satisfies the principle of electrical neutrality for the metal oxide,

wherein the dielectric constant of the dielectric film is more than 320 and the dielectric loss is less than 0.01 at 2.5 GHz.

Claim 20. (previously presented): The memory device as claimed in claim 19, wherein M^1 is Mg, La, or Sr.

Claim 21. (previously presented): The memory device as claimed in claim 20, wherein M^1 is Sr or La.

Claims 22-25. (canceled)

Claim 26. (previously presented): The memory device as claimed in claim 19, wherein $0 < x \leq 0.5$.

Claim 27. (previously presented): The memory device as claimed in claim 19, wherein $0 < y \leq 0.5$.

Claim 28. (canceled)

Claim 29. (previously presented): The memory device as claimed in claim 19, wherein the metal oxide is $(\text{Ba}_{1-x}\text{La}_x)(\text{Ti}_{1-y}\text{Hf}_y)\text{O}_3$, $0 < x \leq 0.5$, and $0 < y \leq 0.5$.

Claim 30. (canceled)

Claim 31. (previously presented): The memory device as claimed in claim 19, wherein the dielectric film with high dielectric constant and low dielectric loss is manufactured from a method of solid state reaction.

Claim 32. (previously presented): The memory device as claimed in claim 19, wherein the dielectric film with high dielectric constant and low dielectric loss is manufactured from a method of liquid phase reaction.

Claim 33. (previously presented): The memory device as claimed in claim 19, wherein the dielectric constant of the dielectric film is more than 950 and the dielectric loss is less than 0.001 at 2.5 GHz.

Claim 34. (previously presented): The memory device as claimed in claim 19, which is a Gbit memory device.

Claim 35. (new): A memory device, comprising:
a dielectric film comprising a quaternary metal oxide having a formula of:
 $(\text{Ba}_{1-x}\text{Sr}_x)(\text{Ti}_{1-y}\text{Ta}_y)\text{O}_3$,
where $0.3 \leq x \leq 0.5$ and $0 < y \leq 0.3$,
wherein the dielectric constant of the dielectric film is more than 320 and the dielectric loss is less than 0.01 at 2.5 GHz.

Claim 36. (new): A memory device, comprising:
a dielectric film comprising a quaternary metal oxide having a formula of:
 $(\text{Ba}_{1-x}\text{La}_x)(\text{Ti}_{1-y}\text{Zr}_y)\text{O}_3$,
where $0 < x \leq 0.5$, and $0 < y \leq 0.5$
wherein the dielectric constant of the dielectric film is more than 320 and the dielectric loss is less than 0.01 at 2.5 GHz.